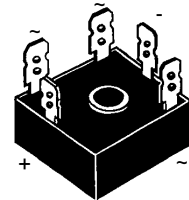
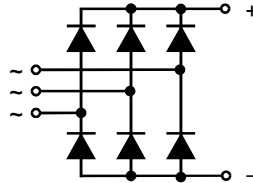


Three Phase Rectifier Bridge

$I_{dAVM} = 35 \text{ A}$
 $V_{RRM} = 1200-1800 \text{ V}$

V_{RSM} V	V_{RRM} V	Type
600	600	VUO 36-06NO8
1200	1200	VUO 36-12NO8
1400	1400	VUO 36-14NO8
1600	1600	VUO 36-16NO8
1800	1800	VUO 36-18NO8



Symbol	Test Conditions	Maximum Ratings
I_{dAV} I_{dAVM}	$T_C = 85^\circ\text{C}$, module	27 A
	$T_C = 62^\circ\text{C}$, module	35 A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	t = 10 ms (50 Hz), sine: 550 A t = 8.3 ms (60 Hz), sine: 600 A
	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz), sine: 500 A t = 8.3 ms (60 Hz), sine: 550 A
I^2t	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	t = 10 ms (50 Hz), sine: 1520 A ² s t = 8.3 ms (60 Hz), sine: 1520 A ² s
	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz), sine: 1250 A ² s t = 8.3 ms (60 Hz), sine: 1250 A ² s
T_{VJ} T_{VJM} T_{stg}		-40...+150 °C 150 °C -40...+150 °C
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	t = 1 min: 2500 V~ t = 1 s: 3000 V~
	M_d	Mounting torque (M5) (10-32 UNF): 2 ± 10 % Nm 18 ± 10 % lb.in.
Weight	typ.	22 g

Features

- Package with 1/4" fast-on terminals
- Isolation voltage 3000 V~
- Planar passivated chips
- Blocking voltage up to 1800 V
- Low forward voltage drop
- UL registered E 72873

Applications

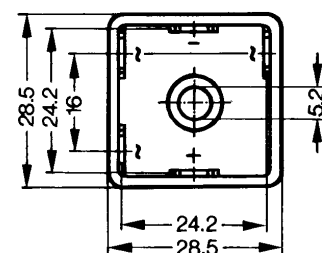
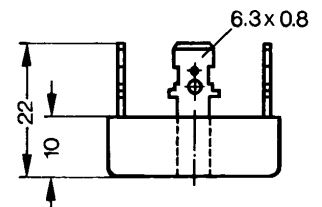
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Advantages

- Easy to mount with one screw
- Space and weight savings
- Improved temperature and power cycling

Symbol	Test Conditions	Characteristic Values
I_R	$T_{VJ} = 25^\circ\text{C}$; $T_{VJ} = T_{VJM}$	$V_R = V_{RRM}$: ≤ 0.3 mA $V_R = V_{RRM}$: ≤ 2.0 mA
	$I_F = 150 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$	≤ 1.7 V
V_{T0}	For power-loss calculations only	0.8 V
r_T		7.4 mΩ
R_{thJC}	per diode; DC current	7.5 K/W
	per module	1.25 K/W
R_{thJH}	per diode; DC current	8.4 K/W
	per module	1.4 K/W
d_s	Creeping distance on surface	12.7 mm
d_A	Creepage distance in air	9.4 mm
a	Max. allowable acceleration	50 m/s ²

Dimensions in mm (1 mm = 0.0394")



Data according to DIN IEC 60747 and refer to a single diode unless otherwise stated. IXYS reserves the right to change limits, test conditions and dimensions.

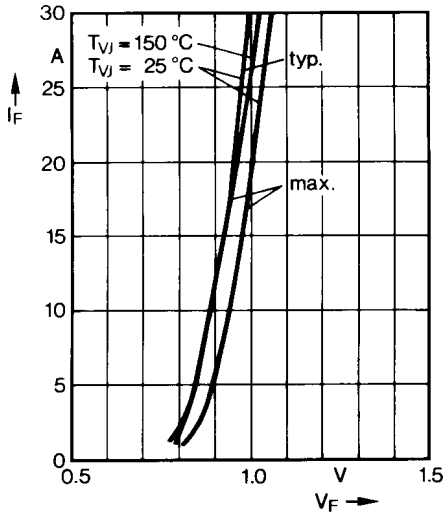


Fig. 1 Forward current versus voltage drop per diode

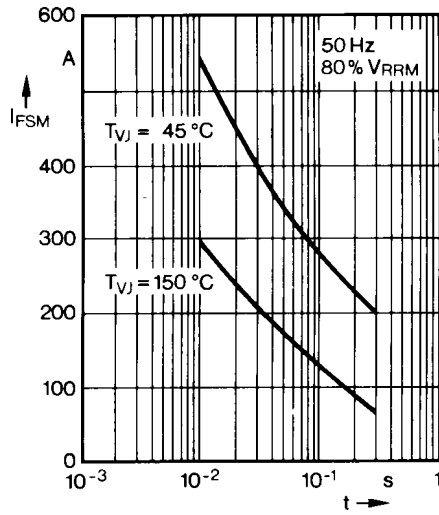


Fig. 2 Surge overload current per diode I_{FSM} : Crest value. t : duration

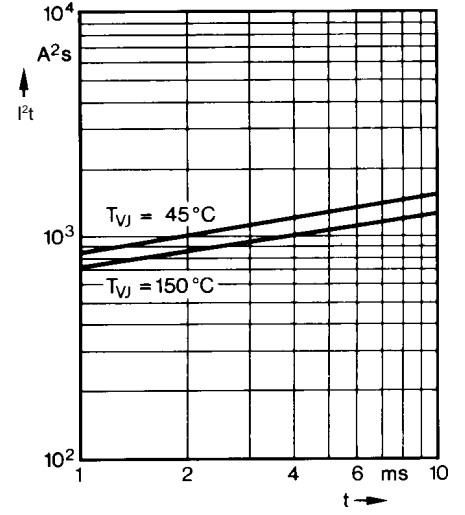


Fig. 3 I^2t versus time (1-10 ms) per diode

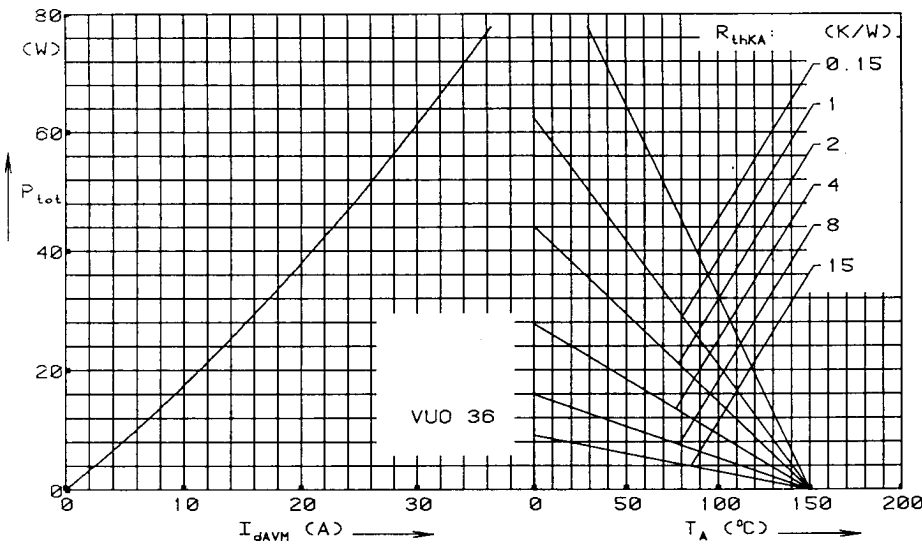


Fig. 4 Power dissipation versus direct output current and ambient temperature

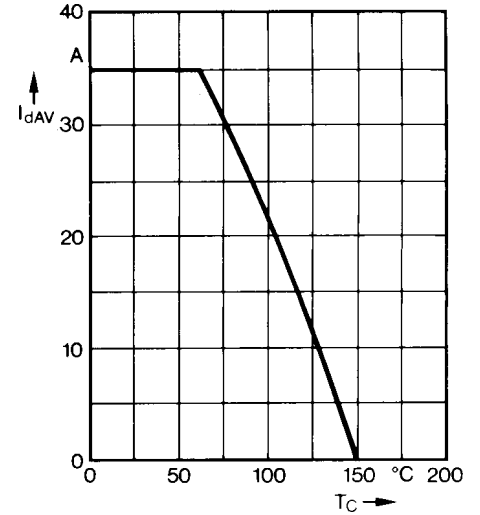


Fig. 5 Maximum forward current at case temperature

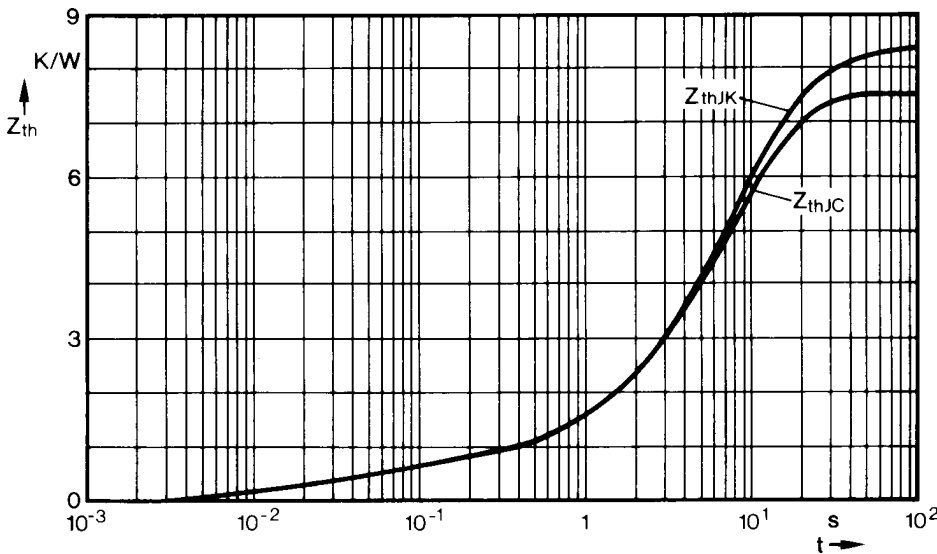


Fig. 6 Transient thermal impedance per diode

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.183	0.032
2	0.528	0.085
3	1.89	5.9
4	4.9	8.3

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.183	0.032
2	0.528	0.085
3	1.89	5.9
4	4.9	8.3
5	0.9	28.0